

# **Inverse Compton X-ray Source for 3D Nanostructured** Metrology



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## Background

As the semiconductor industry continues into the nanoelectronics era following Dennard scaling law, with half-pitch values decreasing below 10 nm, one of the significant challenges lies in the metrology of nanoelectronic devices and 3D interconnect architectures at these sub-nanometer domains [1]. In order to optimize 3-D in-line metrology of critical dimension (CD) geometries for various nanoelectronic applications, non-destructive rapid feedback monitoring system with angstrom resolution [2] is required. One grand challenge for CD-SAXS x-ray sources is meeting both the x-ray energy and flux criteria (similar to a Synchrotron) while maintaining laboratory size. Other problems with x-ray sources include: lack of x-ray energy exceeding 20 keV, low photon number, large beam size, and long scan time. Currently, no x-ray source has been able to solve this problem.

**3D** architecture of nanostructured devices includes: The ability to discern in-line topology of FinFET height and pitch, DRAM pitch, copper wire pitch, low-k dielectric thickness, and interfaces and nano-structures. 3D nanostructured devices create 2D diffraction patterns

List of needs for semiconductor nanostructures [1,3]							
Nanostructure Type	CD [1-2] (nm)				X-ray Energy	Photon Flux	Beam Size
	2017	2019	2021	2023	(keV)	(Ph/s)	(um)
Si FinFET Half-pitch	19	15	12	9.5	20-70	10 <sup>10</sup>	< 100
High-k FinFET	60	6 1	61	57	20.70	1.08	< 100



< 5 nm

# **Results and Modeling**

We have generated narrowband electron beams using structured targets and optical injection. The energy of the electron beam can be tuned while keeping other parameters such as charge, divergence and energy spread constant. Using this approach we have generated x-ray beams that can be tuned in energy keeping other parameters nearly invariant.

Electron-beam spectrum on scintillator for 12 MeV, 30 MeV, and 47 MeV	Table of results for the optical injection experiment with 2 mm jet	Electron beam can be tuned by changing plasma parameters	
	e-beam Energy Divergence, Energy spread, MeV mrad (keV) (MeV) (FWHM) (FWHM)	80 - 70 -	

#### with features discernible through small-angle x-ray scattering





All-laser based Compton x-ray source can meet the requirements for semiconductor metrology

- A viable solution to the CD-SAXS source problem is using all laser-based Inverse Compton scattering (ICS) x-ray source [5, 6]. • Compton scattering utilizes the double Doppler shift from relativistic electrons to create x-rays from visible light. The maximum photon energy is  $E_{\gamma} = 4\gamma^2 \hbar \omega_L$ , where  $\gamma$  is proportional to the kinetic energy of the electrons ( $E_e = \gamma mc^2$ ) and  $\omega_L$  is the frequency of the laser
- All-laser driven ICS at UNL has demonstrated high brightness, high tunability, low spot size, and laboratory size beamline of < 50 m<sup>2</sup> [5]. Using all laser-based system leads to a compact and tunable accelerator that is synchronized to the scattering laser beam.

### **CD-SAXS** Beamline Design

#### **Inverse Compton Scattering**

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High-power laser drives a high-energy electron accelerator. Another pulse from the same laser scatters off the electron beam in a head-on collision and produces a beam of x-rays



**Specs of ICS source for SAXS Beamline** Total Lab Size:  $< 50 \text{ m}^2$ Beamline length: 2 m Laser power: 100 W – 1 kW Peak Power: 50 TW LASER Duration: 30 fs Focused spot size: 20 µm





#### Simulations using a Monte-Carlo code demonstrate source can be scaled to higher fluence for metrology



Electron energy (MeV)

120

100





• Tunable operation of x-ray source is made possible by tunable electron accelerator. Laser driven device can be tuned from 10-100 MeV using a single device and to > 500 MeV using multiple targets. For semiconductor applications single stage x-ray source can be tuned from 10-100 keV. • Photon number depends on specific configuration and can has been shown to span the range 10<sup>7</sup>-10<sup>10</sup> s<sup>-1</sup> using current laser system [5,6]. Significant improvements possible by using latest diode pumped high-average power lasers (e.g., Yb:YAG disk laser).

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following features:		(	
<b>Tunable energy</b>	Energy		
□ Small spot size □ High repotition rate	Bandwidth %		
High repetition rate High brightness	Beam size Time per measurement		
□ Narrowhand x-rays			
Laboratory Size	Divergence/angular spread		
	Laboratory Size		

	(Si+photo resist)	@ 10 keV			@ 20-50 keV
Energy	> 20 keV tunable	5-30		17.45 keV	8-100 keV
Bandwidth %	< 2%	.01			1 %
Beam size	< 100 µm <sup>1,2</sup>	20 um	380 um		5-10 μm
Time per measurement	< 1 min <sup>1,2</sup>				
Divergence/angular spread	< 0.5 <sup>2</sup>	60 µrad		300 µrad	5 mrad (20 keV)
Laboratory Size		21 km <sup>2</sup>			< 50 m <sup>2</sup>

• All-optical Inverse Compton scattering source is a contender for new generation small-angle x-ray scattering sources • ICS university based sources could be the first of its kind for SAXS, USAXS, WAXS nanometrology research



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